



#### 20V SOT26 N-CHANNEL ENHANCEMENT MODE MOSFET

#### **Product Summary**

V <sub>(BR)DSS</sub>	Max R <sub>DS(ON)</sub>	Max I <sub>D</sub> T <sub>A</sub> = +25°C
	0.040Ω @ V <sub>GS</sub> = 4.5V	5.4A
20V	$0.055\Omega$ @ $V_{GS} = 2.5V$	4.6A
	0.075Ω @ V <sub>GS</sub> = 1.8V	4.0A

## **Description and Applications**

This new generation trench MOSFET from Zetex features low onresistance achievable with low gate drive.

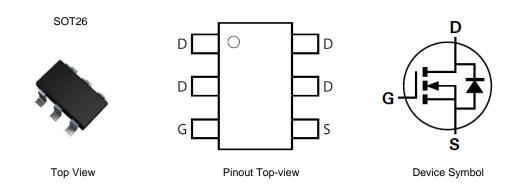
- DC DC Converters
- Power Management Functions
- **Disconnect Switches**
- Motor Control

#### **Features and Benefits**

- Low On-resistance
- Fast Switching Speed
- Low Gate Drive Capability
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

#### **Mechanical Data**

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.015 grams (Approximate)



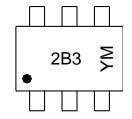
#### Ordering Information (Note 4)

Part Number	Reel Size (inch)	Tape Width (mm)	Quantity Per Reel
ZXMN2B03E6TA	7	8	3000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



2B3 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: C = 2015) M or  $\overline{M}$  = Month (ex: 9 = September)

Date Code Key

Year	2015	5	2016	2017	2018	2019	2020	202	1 20	22 2	2023	2024	2025
Code	С		D	Е	F	G	Н		,	J	K	L	М
Monti	h	Jan	Fek	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	)	1	2	3	4	5	6	7	8	9	0	N	D

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## **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

	Characteristic		Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	20	V
Gate-Source Voltage			V <sub>GS</sub>	±8	V
		$T_A = +25^{\circ}C \text{ (Note 6)}$		5.4	
Continuous Drain Current	$V_{GS} = 4.5V$	$T_A = +70^{\circ}C \text{ (Note 6)}$	lD	4.3	Α
		$T_A = +25^{\circ}C \text{ (Note 5)}$		4.3	
Pulsed Drain Current (Note 7	)		I <sub>DM</sub>	26	Α
Continuous Source Current (Body Diode) (Note 6)			I <sub>S</sub>	2.8	А
Pulsed Source Current (Body	Diode) (Note	7)	I <sub>SM</sub>	26	A

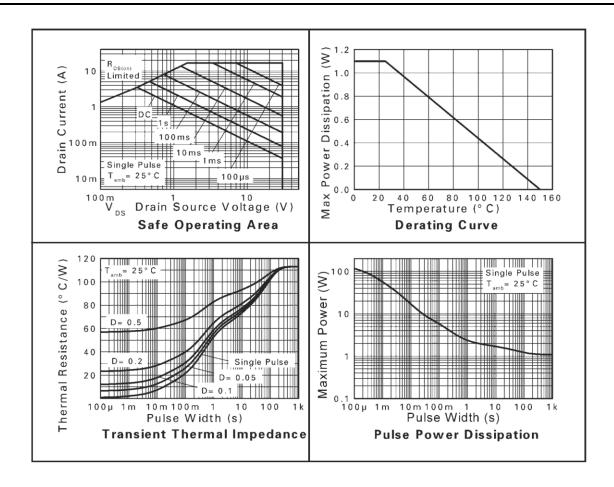
#### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation at T <sub>A</sub> = +25°C (Note 5) Linear derating factor (Note 5)	P <sub>D</sub>	1.1 8.8	W mW/°C
Power Dissipation at T <sub>A</sub> = +25°C (Note 6) Linear derating factor (Note 6)	P <sub>D</sub>	1.7 13.7	W mW/°C
Junction to Ambient (Note 5)	$R_{ hetaJA}$	113	°C/W
Junction to Ambient (Note 6)	$R_{ heta JA}$	73	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes:

- 5. For a device surface mounted on 25mm x 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- 6. For a device surface mounted on FR-4 PCB measured at t ≤ 10 secs.
- 7. Repetitive rating 25mm x 25mm FR-4 PCB, D = 0.02, pulse width 300µs pulse width limited by maximum junction temperature.

#### Thermal Characteristics



March 2015



## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

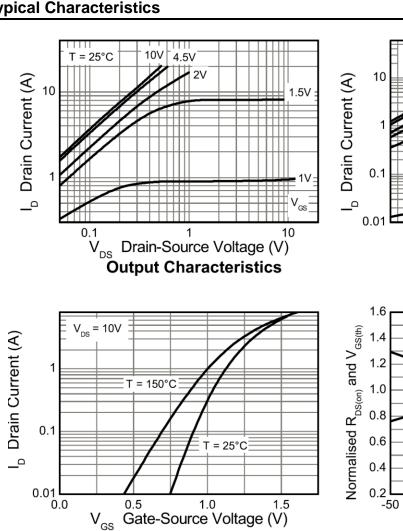
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-source Breakdown Voltage	BV <sub>DSS</sub>	20	1	1	٧	$I_D = 250 \mu A, V_{GS} = 0V$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_		1	μΑ	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-body Leakage	I <sub>GSS</sub>	_	_	100	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$	
Diode Forward Voltage (Note 8)	$V_{SD}$	_	0.67	0.95	V	$T_J = +25^{\circ}C$ , $I_S = 1.8A$ , $V_{GS} = 0V$	
ON CHARACTERISTICS							
Gate-source Threshold Voltage	V <sub>GS(th)</sub>	0.4	_	1.0	V	$I_D = 250 \mu A$ , $V_{DS} = V_{GS}$	
				0.040		$V_{GS} = 4.5V, I_D = 4.3A$	
Static Drain-source On-state Resistance (Note 8)	R <sub>DS(ON)</sub>	_	_	0.055	Ω	$V_{GS} = 2.5V, I_D = 3.7A$	
· · ·	, ,			0.075		$V_{GS} = 1.8V, I_D = 3.2A$	
Forward Transconductance (Notes 8 & 10)	g <sub>fs</sub>	_	13.5	_	S	$V_{DS} = 10V, I_D = 4.3A$	
DYNAMIC CHARACTERISTICS (Notes 9 & 10)							
Input Capacitance	Ciss	_	1160	_	pF	), 40V, V, 0V,	
Output Capacitance	Coss	_	210	1	рF	$V_{DS} = 10V, V_{GS} = 0V$ - f = 1MHz	
Reverse Transfer Capacitance	Crss	_	136	_	pF	1 = 1101112	
Total Gate Charge	$Q_g$	_	14.5	_	nC	15/// 40//	
Gate-source Charge	$Q_{gs}$	_	2.0	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V$	
Gate-drain Charge	$Q_{gd}$	_	2.8	_	nC	$I_D = 4.3A$	
Reverse Recovery Time (Note 10)	t <sub>rr</sub>	_	10.8	_	ns	T <sub>J</sub> = +25°C, I <sub>F</sub> =2.8A,	
Reverse Recovery Charge (Note 10)	Qrr	_	3.4	_	nC	di/dt= 100A/µs	
Turn-on Delay Time	t <sub>d(on)</sub>	_	2.9	_	ns		
Turn-on Rise Time	t <sub>r</sub>	_	6.4	_	ns	$V_{DD} = 10V, V_{GS} = 4.5V$	
Turn-off Delay Time	t <sub>d(off)</sub>	_	16.0	_	ns	$I_D = 1A, R_G = 6.0\Omega$	
Turn-off Fall Time	t <sub>f</sub>	_	11.2	_	ns	]	

Notes:

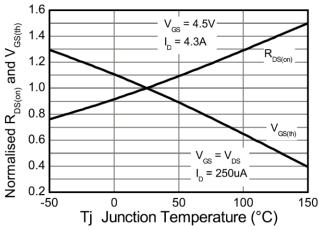
- 8. Measured under pulsed conditions. Width=300µs. Duty cycle ≤ 2%.
  9. Switching characteristics are independent of operating junction temperature.
  10. For design aid only, not subject to production testing.



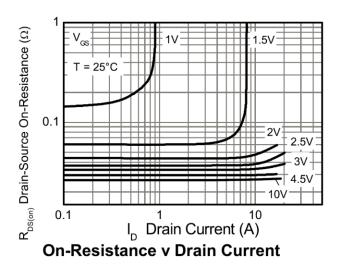
# **Typical Characteristics**

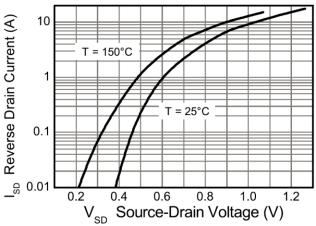


T = 150°C 0.5V 0.1 Drain-Source Voltage (V) **Output Characteristics** 



**Typical Transfer Characteristics Normalised Curves v Temperature** 

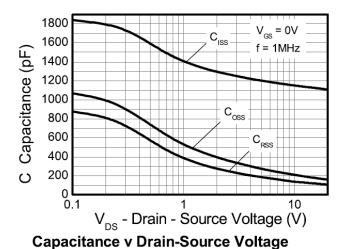


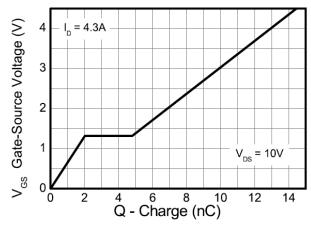


Source-Drain Diode Forward Voltage



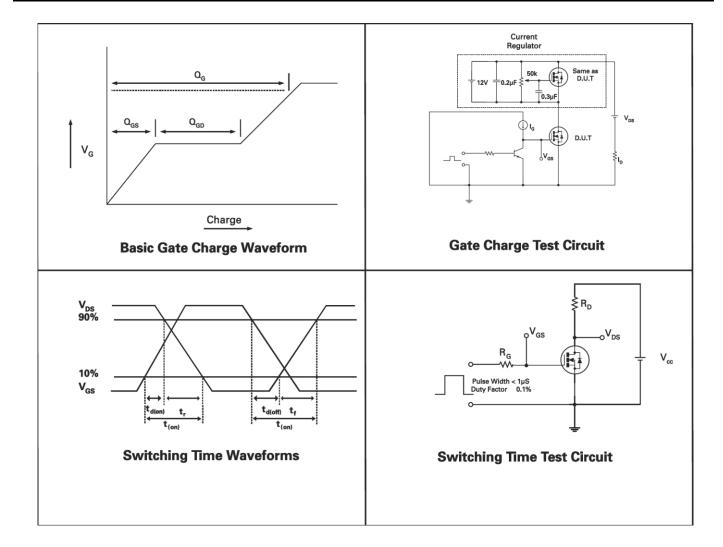
# Typical Characteristics (Cont.)





Gate-Source Voltage v Gate Charge

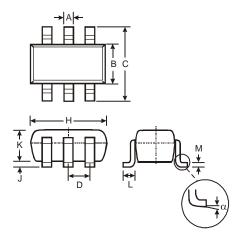
## **Test Circuits**





# **Package Outline Dimensions**

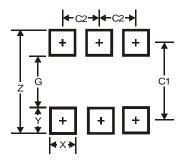
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT26					
Dim	Min	Max	Тур		
Α	0.35	0.50	0.38		
В	1.50	1.70	1.60		
O	2.70	3.00	2.80		
D	_	_	0.95		
Н	2.90	3.10	3.00		
J	0.013	0.10	0.05		
K	1.00	1.30	1.10		
٦	0.35	0.55	0.40		
M	0.10	0.20	0.15		
α	0°	8°			
All Dimensions in mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Υ	0.80
C1	2.40
C2	0.95



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